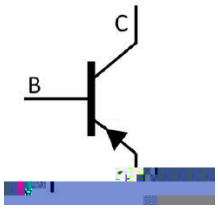
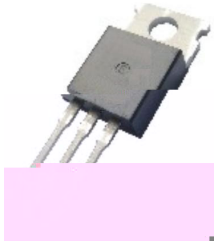
TO-220 PNP Silicon PNP transistor in a TO-220 Plastic Package.

BR2N6488

Complement to BR2N6488.

Use in general–purpose amplifier and switching applications.





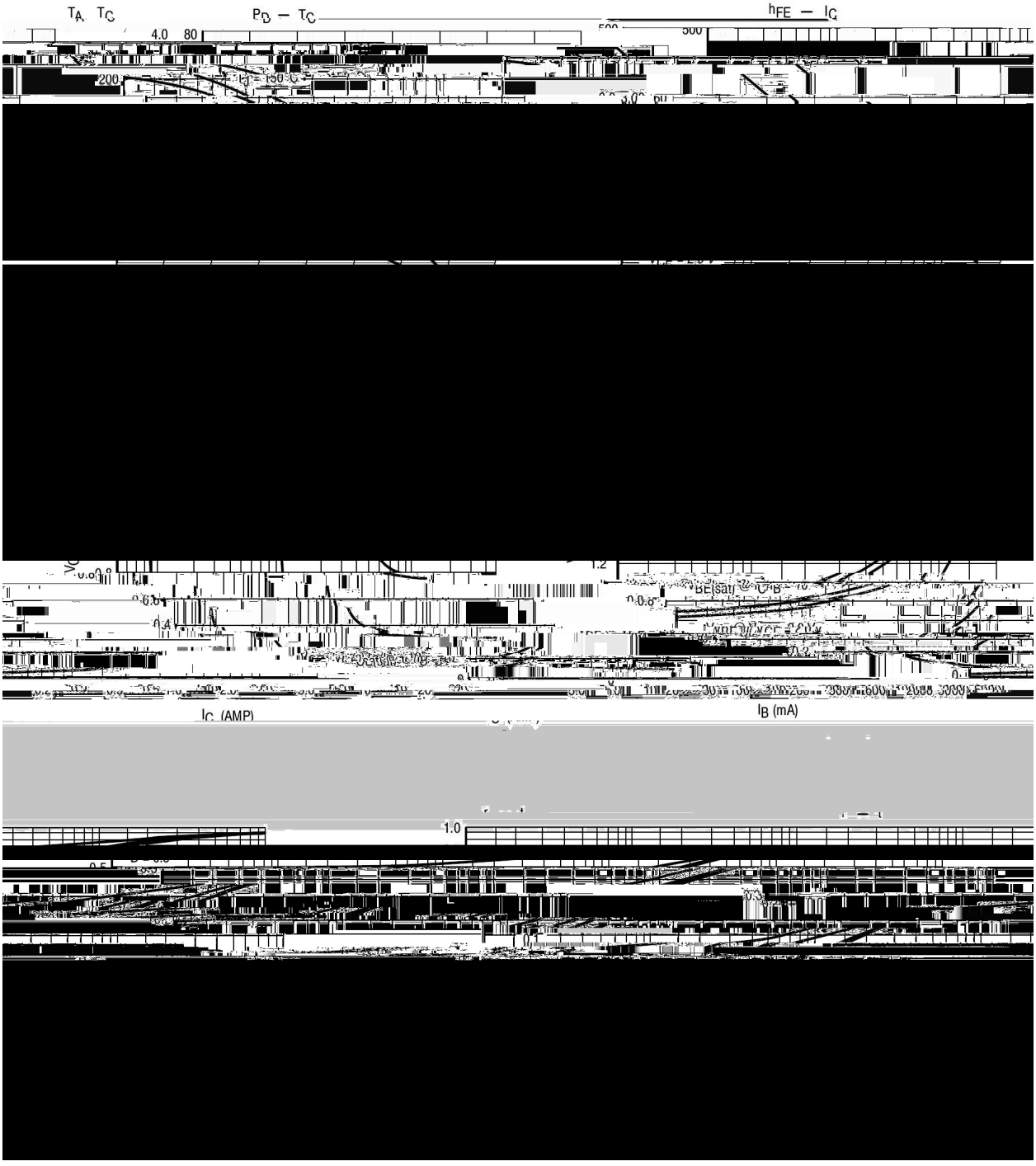
PIN1 Base PIN 2 Collector PIN 3 Emitter

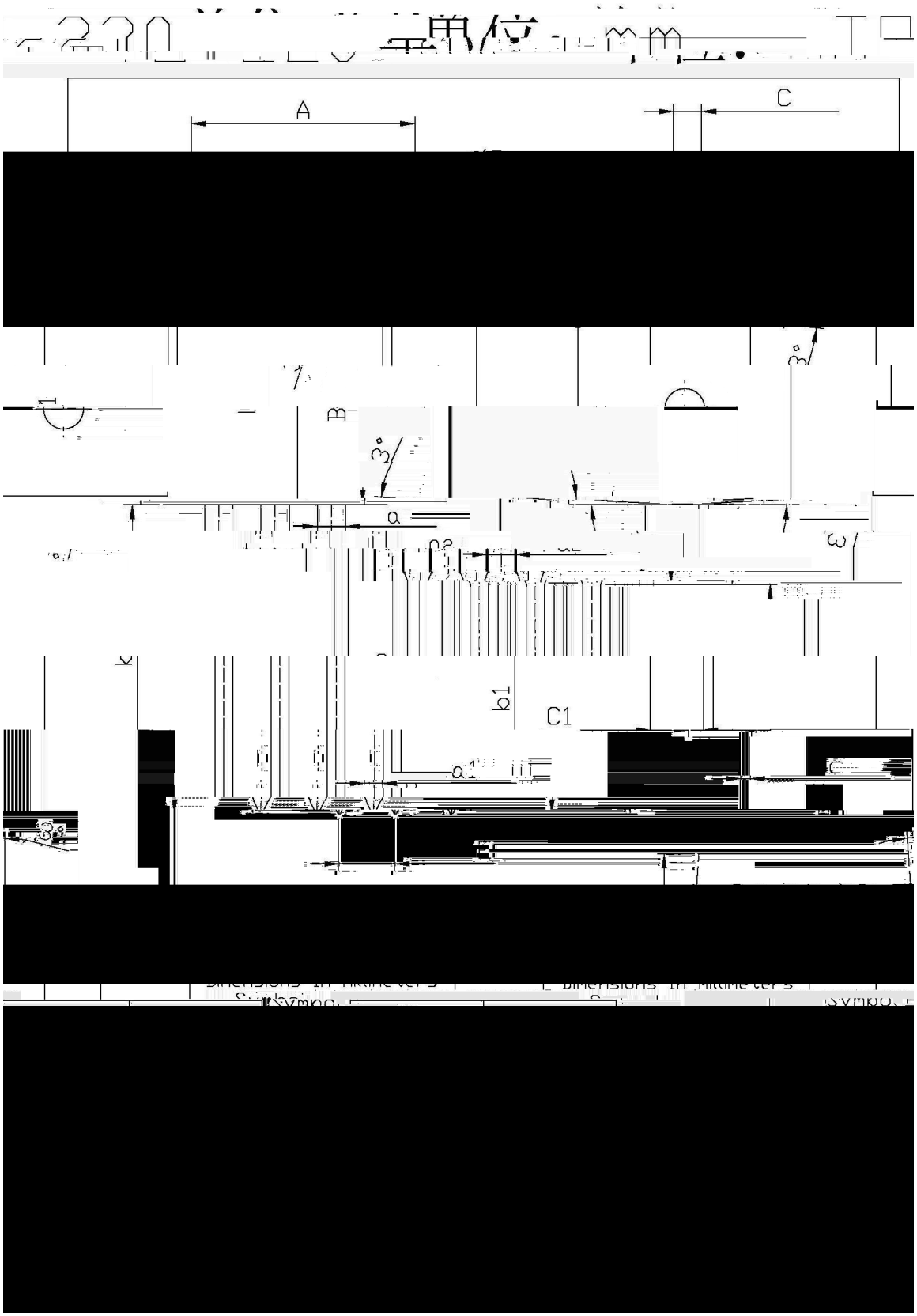
See Marking Instructions.

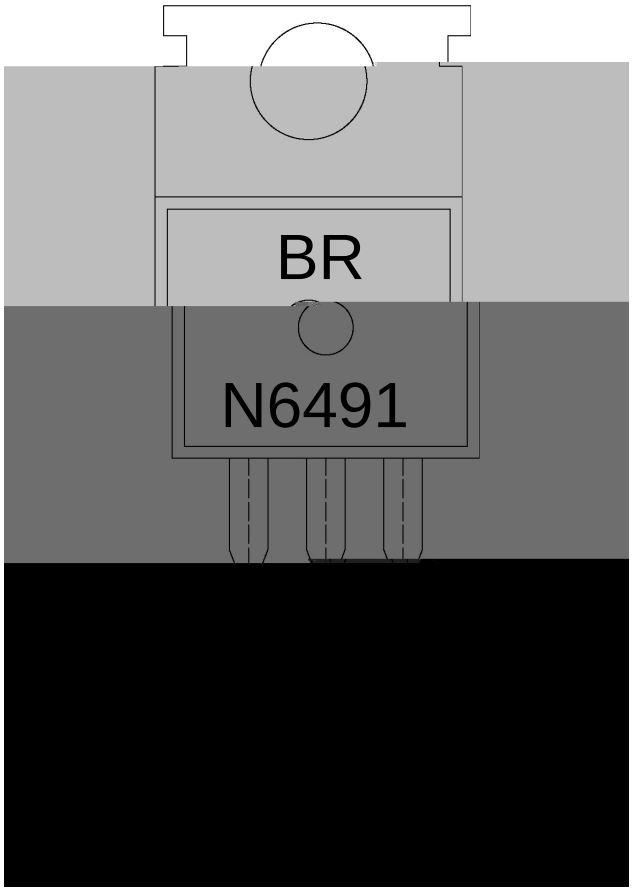
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-90	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current	I_B	-5.0	A
Total Power Dissipation	$P_D(T_C=25\ )$	75	W
	$P_D(T_A=25\ )$	1.8	W
Operating and Storage Junction Temperature Range	$T_j\ T_{stg}$	-65 +150	
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.67	/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	70	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	I_C=-200mA I_B=0	-80			V
Collector Emitter Sustaining Voltage	V_{CEX}	I_C=-200mA V_{BE}=-1.5V	-90			V
Collector Cut-Off Current	I_{CEX}	V_{CB}=-85V $V_{BE(off)}$=-1.5V			-500	μA
		V_{CB}=-80V $V_{BE(off)}$=-1.5V T_C=150			-5.0	μA
Collector Cut-Off Current	I_{CEO}	V_{CE}=-40V I_B=0			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-1.0	mA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-4.0V I_C=-5.0A	20		150	
	$h_{FE(2)}$	V_{CE}=-4.0V I_C=-15A	5.0			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-5.0A I_B=-0.5A			-1.3	V
		I_C=-15A I_B=-5.0A			-3.5	V

Base to Emitter On Voltage V


TA, TC
PD — TC
hFE — IC
4.0
80
200
500
300
1.2
0.6
0.4
IC (AMP)
IB (mA)
1.0


A
C
B
3°
3°
a
b1
C1
a1



BR

N6491

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Note:

BR:	Company Code
N6491:	Product Type.
****:	Lot No. Code, code change with Lot No.